

REFERENCES

1. C.M. Osburn and D.W. Ormond, *J. Electrochem. Soc.: Solid-state science and technology* **119**, 597 (1972).
2. T. Abe, Y. Kato, *Jpn. J. Appl. Phys.*, **32**, 1879 (1993)
3. D.R. Wolters, J.J. Van Der Schoot, *Philips Journal of Research* **40**, 115 (1985).
4. W. Kern, *RCA Review*, **34**, 655 (1973).
5. W.J. Shannon, *RCA Review*, **31**, 431 (1970).
6. S. Mahajan and K.S. Sree Harsha, *Principles of growth and processing of semiconductors*, 1st edition, 298-330 (1998).
7. M.S. Tyagi, *Introduction to semiconductor materials and devices*, John Wiley & Sons, 583-588 (1991).
8. Deal, B.E. and A.S. Grove, *J. Apply. Phys.* **36**, 3770 (1965).
9. T. Hori, *Gate Dielectrics and MOS ULSIs*, Springer, **34**, 174 (1997).
10. M. Itsumi, H. Akiya, T. Ueki, M. Tomita and M. Yamawaki, *Jpn. J. Appl. Phys* **35**, 812 (1996).
11. M. Miyazaki, S. Miyazaki, Y. Yanase, T. Ochiai and T. Shigemitsu, *Jpn. J. Appl. Phys.* **34**, 6303 (1995).
12. M. Kato, T. Yoshida, Y. Ikeda and Y. Kitagawara, *Jpn. J. Appl. Phys.* **35**, 5597 (1996).
13. H. Nishikawa, T. Tanaka, Y. Yanase, M. Hourai, M. Sano and H. Tsuya, *Jpn. J. Appl. Phys.* **36**, 6595 (1997).

14. J. Ryuta, E. Morita, T. Tanaka and Y. Shimanuki, *Jpn. J. Appl. Phys.* **29**, L1947 (1990).
15. J. Ryuta, E. Morita, T. Tanaka and Y. Shimanuki, *Jpn. J. Appl. Phys.* **31**, L293 (1992).
16. M. Itsumi, H. Akiya, T. Ueki, M. Tomita and M. Yamawaki, *J. App. Phys.* **78**, 5984 (1995).
17. H. Yamagishi, I. Fusegawa, N. Fujimaki and M. Katayama, *Semiconductor Sci. Technol.* **A135**, 7 (1992).
18. T. Ueki, M. Itsumi and T. Takeda, 1996 Int. Conf. Solid State Devices and Materials, Yokohama, LA-1, 862 (1996).
19. M. Nishimura, S. Yoshino, H. Motoura, S. Shimura, T. Mcchedlidze and T. Hikone, *J. Electrochem. Soc.* **143**, L243 (1996).
20. M. Itsumi, M. Tomita, and M. Yamawaki, *J. App. Phys.* **78**, 1940 (1995).
21. T. Ueki, M. Itsumi and T. Takeda, *Jpn. J. Appl. Phys.* **37**, 1667 (1998).
22. S. Sadamitsu, S. Umeno, Y. Koike, M. Hourai, S. Sumita and T. Shigemitsu, *Jpn. J. Appl. Phys.* **32**, 3675 (1993).
23. M. Kimura and T. Abe, *Jpn. J. Cryst. Growth* **19**, 38 (1992).
24. P.J. Roksnoer and M. M. B. Van Den Boom, *J. Cryst. Growth* **53**, 563 (1981).
25. S.E. Bradshaw and J. Goorissen, *J. Cryst. Growth* **48**, 514 (1980).
26. H. Yamagishi, I. Fusegawa, N. Fujimaki, and M. Katayama, *Semicond. Sci. Technol.* **A7**, 135 (1992).
27. K. Tempelhoff, F. Spiegelberg, R. Gleichmann and D. Wruck, *Phys. Status. Solidi* **A56**, 213 (1979).

28. S.Oka and M.Katayama, Jpn. J. Appl. Phys, **36**, 1995 (1997).
29. M. Itsumi, H. Akiya, T. Ueki, M. Tomita and M. Yamawaki, J. Electrochem. Soc., **144**, 600 (1997).
30. M. Itsumi and F. Kiyosumi, Appl. Phys. Lett., **40**, 496 (1982).
31. O. Nakajima, N. Shiono, S. Muramoto and C. Hashimoto, Jpn. J. Appl. Phys **18**, 943 (1979).
32. M. Itsumi, O. Nakajima and N. Shiono, J. Appl. Phys. **72**, 2185 (1992).
33. O. Nakajima, M. Itsumi, N. Shiono, and Y. Yoriume, Jpn. J. Appl. Phys. **30**, 512. (1979).
34. M. Itsumi, Y. Omura, K. Imai, T. Ueki, H. Akiya, M. Tomita and M. Yamawaki, J. Electrochem. Soc., **143**, 2357 (1996).
35. M. Itsumi, Y. Yoriume, O. Nakajima, and N. Shiono, Jpn. Soc. Appl. Phys., **3**, 553 (1980).
36. H. Ishii, S. Shiratake, K. Oka, K. Motonami, T. Koyama and J. Izumitani, Jpn. J. Appl. Phys. **35**, L1385 (1996).
37. Christopher M.A. Brett, Aria Maria Oliveira Brett, *Electrochemistry - principles, methods and applications*, Oxford University Press, 25 (1993).
38. SKOOG, WEST, HOLLER, "Analytical Chemistry – An introduction", 6th edition, Saunders College Publishing, 357 – 378 (1994).
39. N. Shiono, O. Nakajima, and C. Hashimoto, J. Electrochem. Soc. **130**, 138 (1983).
40. J. C. Lee, I. C. Chen, and C. Hu, IEE Trans. Electron Devices **ED-35**, 2268 (1988),

-
41. Y. Horaki, IEE Trans. Electron Devices ED-**35**, 1299 (1988).
 42. K. Yamabe, K. Taniguchi, and Y. Matsushita, Proceedings of the International Reliability Physics Symposium, Phoenix, April 5-7, 1983 (IEEE, New York, 1983), p.184.
 43. Y. Satoh, T. Shiota, Y. Murakami, T. Shingyouji and H. Furuya, J. Appl. Phys. **79**, 7944 (1996).
 44. J.G Trump and K.A. Wright, Mat. Res. Bull. **6**, 1075 (1971).
 45. W.R. Runyan and T.J. Shaffner, "Semiconductor measurements and instrumentation", 2nd edition, Mc GrawHill, 386-424 (1997).
 46. DimensionTM 5000 Instruction Manual (AFM)
 47. W.P. Lee, H.K. Yow and T.Y. Tou, technical report on "Detection and size determination of Crystal Originated Particles" on silicon wafer surface using optical scattering technique integrated to an Atomic Force Microscope", S.E.H. (M) Sdn. Bhd. (2001).
 48. S.Mahajan and K.S.S. Harsha, "Principles of growth and processing of semiconductors", 1st edt., 122-130 (1999).
 49. R.C Weast, D.R. Lide, Handbook of Chemistry and Physics, CRC Press, 70th edition (1990).